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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104lfafa-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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Pin count	Package	Fields of Application Note	Ordering Part Number
64 pins	64-pin plastic LQFP	A	R5F104LCAFA#V0, R5F104LDAFA#V0, R5F104LEAFA#V0, R5F104LFAFA#V0,
	(12 × 12 mm, 0.65 mm pitch)		R5F104LGAFA#V0, R5F104LHAFA#V0, R5F104LJAFA#V0
			R5F104LCAFA#X0, R5F104LDAFA#X0, R5F104LEAFA#X0, R5F104LFAFA#X0, R5F104LGAFA#X0, R5F104LHAFA#X0, R5F104LJAFA#X0
			R5F104LKAFA#30, R5F104LLAFA#30
			R5F104LKAFA#50, R5F104LLAFA#50
		D	R5F104LCDFA#V0, R5F104LDDFA#V0, R5F104LEDFA#V0, R5F104LFDFA#V0,
			R5F104LGDFA#V0, R5F104LHDFA#V0, R5F104LJDFA#V0 R5F104LCDFA#X0, R5F104LDDFA#X0, R5F104LEDFA#X0, R5F104LFDFA#X0,
			R5F104LGDFA#X0, R5F104LHDFA#X0, R5F104LJDFA#X0
		G	R5F104LCGFA#V0, R5F104LDGFA#V0, R5F104LEGFA#V0, R5F104LFGFA#V0, R5F104LGGFA#V0, R5F104LHGFA#V0, R5F104LJGFA#V0
			R5F104LCGFA#X0, R5F104LDGFA#X0, R5F104LEGFA#X0, R5F104LFGFA#X0, R5F104LGGFA#X0, R5F104LHGFA#X0, R5F104LJGFA#X0
			R5F104LKGFA#30, R5F104LLGFA#30
			R5F104LKGFA#50, R5F104LLGFA#50
	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	A	R5F104LCAFB#V0, R5F104LDAFB#V0, R5F104LEAFB#V0, R5F104LFAFB#V0, R5F104LGAFB#V0, R5F104LHAFB#V0, R5F104LJAFB#V0
	(10 × 10 mm, 0.0 mm phon)		R5F104LCAFB#X0, R5F104LDAFB#X0, R5F104LEAFB#X0, R5F104LFAFB#X0,
			R5F104LGAFB#X0, R5F104LHAFB#X0, R5F104LJAFB#X0
			R5F104LKAFB#30, R5F104LLAFB#30
			R5F104LKAFB#50, R5F104LLAFB#50
		D	R5F104LCDFB#V0, R5F104LDDFB#V0, R5F104LEDFB#V0, R5F104LFDFB#V0, R5F104LGDFB#V0, R5F104LHDFB#V0, R5F104LJDFB#V0
			R5F104LCDFB#X0, R5F104LDDFB#X0, R5F104LEDFB#X0, R5F104LFDFB#X0, R5F104LGDFB#X0, R5F104LHDFB#X0, R5F104LJDFB#X0
		G	R5F104LCGFB#V0, R5F104LDGFB#V0, R5F104LEGFB#V0, R5F104LFGFB#V0, R5F104LGGFB#V0, R5F104LHGFB#V0, R5F104LJGFB#V0
			R5F104LCGFB#X0, R5F104LDGFB#X0, R5F104LEGFB#X0, R5F104LFGFB#X0, R5F104LGGFB#X0, R5F104LHGFB#X0, R5F104LJGFB#X0
			R5F104LKGFB#30, R5F104LLGFB#30
			R5F104LKGFB#50, R5F104LLGFB#50
	64-pin plastic FLGA (5 × 5 mm, 0.5 mm pitch)	А	R5F104LCALA#U0, R5F104LDALA#U0, R5F104LEALA#U0, R5F104LFALA#U0, R5F104LGALA#U0, R5F104LHALA#U0, R5F104LJALA#U0
	(**************************************		R5F104LCALA#W0, R5F104LDALA#W0, R5F104LEALA#W0, R5F104LFALA#W0, R5F104LGALA#W0, R5F104LHALA#W0, R5F104LJALA#W0
			R5F104LKALA#U0, R5F104LLALA#U0
			R5F104LKALA#W0, R5F104LLALA#W0
		G	R5F104LCGLA#U0, R5F104LDGLA#U0, R5F104LEGLA#U0, R5F104LFGLA#U0,
			R5F104LGGLA#U0, R5F104LHGLA#U0, R5F104LJGLA#U0, R5F104LKGLA#U0,
			R5F104LLGLA#U0
			R5F104LCGLA#W0, R5F104LDGLA#W0, R5F104LEGLA#W0, R5F104LFGLA#W0, R5F104LGGLA#W0, R5F104LHGLA#W0, R5F104LJGLA#W0, R5F104LKGLA#W0,
			R5F104LLGLA#W0
	64-pin plastic LQFP (14 × 14 mm, 0.8 mm pitch)	A	R5F104LCAFP#V0, R5F104LDAFP#V0, R5F104LEAFP#V0, R5F104LFAFP#V0, R5F104LGAFP#V0, R5F104LHAFP#V0, R5F104LJAFP#V0
	(14 × 14 mm, 0.0 mm piton)		R5F104LCAFP#X0, R5F104LDAFP#X0, R5F104LEAFP#X0, R5F104LFAFP#X0,
			R5F104LGAFP#X0, R5F104LHAFP#X0, R5F104LJAFP#X0
		D	R5F104LCDFP#V0, R5F104LDDFP#V0, R5F104LEDFP#V0, R5F104LFDFP#V0,
			R5F104LGDFP#V0, R5F104LHDFP#V0, R5F104LJDFP#V0
			R5F104LCDFP#X0, R5F104LDDFP#X0, R5F104LEDFP#X0, R5F104LFDFP#X0, R5F104LGDFP#X0, R5F104LHDFP#X0, R5F104LJDFP#X0
		G	R5F104LCGFP#V0, R5F104LDGFP#V0, R5F104LEGFP#V0, R5F104LFGFP#V0,
			R5F104LGGFP#V0, R5F104LHGFP#V0, R5F104LJGFP#V0
	1		R5F104LCGFP#X0, R5F104LDGFP#X0, R5F104LEGFP#X0, R5F104LFGFP#X0,

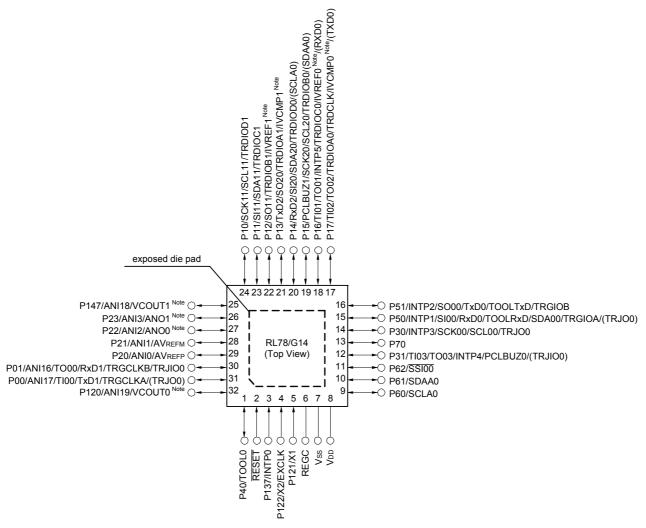
Note

For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.2 32-pin products

• 32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)



Note Mounted on the 96 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).
- Remark 3. It is recommended to connect an exposed die pad to Vss.

1.4 Pin Identification

ANI0 to ANI14,: RxD0 to RxD3: Receive data Analog input ANI16 to ANI20 SCK00, SCK01, SCK10,: Serial clock input/output ANO0, ANO1: Analog output SCK11, SCK20, SCK21, AVREFM: A/D converter reference SCK30, SCK31 potential (- side) input SCLA0, SCLA1,: Serial clock input/output AVREFP: A/D converter reference SCL00, SCL01, SCL10, SCL11,: Serial clock output potential (+ side) input SCL20, SCL21, SCL30, EVDD0, EVDD1: SCI 31 Power supply for port EVsso, EVss1: Ground for port SDAA0, SDAA1, SDA00,: Serial data input/output EXCLK: External clock input SDA01, SDA10, SDA11, SDA20, SDA21, SDA30, (main system clock) EXCLKS: External clock input SDA31 (subsystem clock) SI00, SI01, SI10, SI11,: Serial data input INTP0 to INTP11: SI20, SI21, SI30, SI31 External interrupt input IVCMP0, IVCMP1: Comparator input SO00, SO01, SO10,: Serial data output IVREF0, IVREF1: Comparator reference input SO11, SO20, SO21, KR0 to KR7: SO30, SO31 Key return P00 to P06: Port 0 SSI00: Serial interface chip select input P10 to P17: Port 1 TI00 to TI03,: Timer input P20 to P27: Port 2 TI10 to TI13 P30, P31: Port 3 TO00 to TO03,: Timer output P40 to P47: Port 4 TO10 to TO13, TRJ00 P50 to P57: Port 5 TOOL0: Data input/output for tool P60 to P67: Port 6 TOOLRxD, TOOLTxD: Data input/output for external device P70 to P77: Port 7 TRDCLK, TRGCLKA,: Timer external input clock P80 to P87: Port 8 **TRGCLKB** P100 to P102: Port 10 TRDIOA0, TRDIOB0,: Timer input/output P110, P111: Port 11 TRDIOCO, TRDIODO, P120 to P124: Port 12 TRDIOA1, TRDIOB1, P130, P137: Port 13 TRDIOC1, TRDIOD1, P140 to P147: Port 14 TRGIOA, TRGIOB, TRJIO0 P150 to P156: Port 15 TxD0 to TxD3: Transmit data PCLBUZ0, PCLBUZ1: VCOUT0, VCOUT1: Comparator output Programmable clock output/buzzer output ADD. Power supply REGC: Vss: Ground Regulator capacitance RESET: X1, X2: Reset Crystal oscillator (main system clock) Real-time clock correction RTC1HZ: XT1. XT2: Crystal oscillator (subsystem clock)

clock

(1 Hz) output

[48-pin, 64-pin products (code flash memory 384 KB to 512 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

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		48-pin 64-pin				
I	tem	R5F104Gx	R5F104Lx			
		(x = K, L)	(x = K, L)			
Code flash memory	(KB)	384 to 512	384 to 512			
Data flash memory (KB)	8	8			
RAM (KB)		32 to 48 Note	32 to 48 Note			
Address space		1 MB				
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)				
	High-speed on-chip oscillator clock (fін)	HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)				
Subsystem clock	•	XT1 (crystal) oscillation, external subsyste	m clock input (EXCLKS) 32.768 kHz			
Low-speed on-chip	oscillator clock	15 kHz (TYP.): VDD = 1.6 to 5.5 V				
General-purpose rec	gister	8 bits × 32 registers (8 bits × 8 registers × 4	banks)			
Minimum instruction	execution time	0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)				
		0.05 μs (High-speed system clock: fмx = 20 MHz operation)				
		30.5 μs (Subsystem clock: fsuB = 32.768 k	Hz operation)			
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8 Multiplication (8 bits × 8 bits, 16 bits × 16 bits) Multiplication and Accumulation (16 bits > 16 bits) Rotate, barrel shift, and bit manipulation etc. 	oits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 < 16 bits + 32 bits)			
I/O port	Total	44	58			
	CMOS I/O	34	48			
	CMOS input	5	5			
	CMOS output	1	1			
	N-ch open-drain I/O (6 V tolerance)	4	4			
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Tir	ner RD: 2 channels, Timer RG: 1 channel)			
	Watchdog timer	1 channel				
	Real-time clock (RTC)	1 channel				
	12-bit interval timer	1 channel				
	Timer output	Timer outputs: 14 channels PWM outputs: 9 channels				
	RTC output	1 • 1 Hz (subsystem clock: fsub = 32.768 kHz)				

(Note is listed on the next page.)

Note

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xL (x = G, L, M, P): Start address F3F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

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		40 :	(2/2)				
		48-pin	64-pin				
Item		R5F104Gx	R5F104Lx				
		(x = K, L)	(x = K, L)				
Clock output/buzzer outp	out	2	2				
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5	5 MHz, 5 MHz, 10 MHz				
		(Main system clock: fMAIN = 20 MHz operation					
		• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.09					
		(Subsystem clock: fsub = 32.768 kHz opera	· T				
8/10-bit resolution A/D co	onverter	10 channels	12 channels				
D/A converter		2 channels					
Comparator		2 channels					
Serial interface		[48-pin products]					
		CSI: 2 channels/UART (UART supporting LI	N-bus): 1 channel/simplified I ² C: 2 channels				
		CSI: 1 channel/UART: 1 channel/simplified I	² C: 1 channel				
		CSI: 2 channels/UART: 1 channel/simplified	I ² C: 2 channels				
		[64-pin products]					
			• CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 2 channels				
		• CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels					
		CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels					
	I ² C bus	1 channel	1 channel				
Data transfer controller (I	DTC)	32 sources 33 sources					
Event link controller (ELC	C)	Event input: 22					
		Event trigger output: 9					
Vectored interrupt	Internal	24	24				
sources	External	10	13				
Key interrupt		6	8				
Reset		Reset by RESET pin					
l		Internal reset by watchdog timer					
		Internal reset by power-on-reset					
		Internal reset by voltage detector					
		Internal reset by illegal instruction execution	Note				
		Internal reset by RAM parity error					
		Internal reset by illegal-memory access					
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C)					
		1.51 ±0.06 V (TA = -40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (TA = -40 to +85°C)					
		• Power-down-reset: 1.50 \pm 0.04 V (TA = -40 to +85°C) 1.50 \pm 0.06 V (TA = -40 to +105°C)					
Voltage detector		1.60 V to 4.06 V (14 stages)					
On-chip debug function		Provided					
Power supply voltage		V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C)					
1 Ower Supply Voltage		V _{DD} = 2.4 to 5.5 V (T _A = -40 to +105°C)					
Operating ambient temper	erature	, ,	D: Industrial applications)				
	Jature	T _A = -40 to +85°C (A: Consumer applications, D: Industrial applications), T _A = -40 to +105°C (G: Industrial applications)					
		(3. madound applications	,				

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

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			(212)			
		80-pin	100-pin			
lt.	tem	R5F104Mx	R5F104Px			
		(x = F to H, J)	(x = F to H, J)			
Clock output/buzz	zer output	2	2			
		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.3 (Main system clock: fmain = 20 MHz operations 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.09 (Subsystem clock: fsub = 32.768 kHz operations) 	on) 96 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz			
8/10-bit resolution	A/D converter	17 channels	20 channels			
D/A converter		2 channels	2 channels			
Comparator		2 channels	2 channels			
Serial interface		[80-pin, 100-pin products] • CSI: 2 channels/UART (UART supporting LI • CSI: 2 channels/UART: 1 channel/simplified • CSI: 2 channels/UART: 1 channel/simplified • CSI: 2 channels/UART: 1 channel/simplified	l ² C: 2 channels l ² C: 2 channels			
	I ² C bus	2 channels	2 channels			
Data transfer con	troller (DTC)	39 sources	39 sources			
Event link controll	er (ELC)	Event input: 26 Event trigger output: 9				
Vectored inter-	Internal	32	32			
rupt sources	External	13	13			
Key interrupt	1	8	8			
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Internal reset by RAM parity error Internal reset by illegal-memory access	Note			
Power-on-reset circuit		 Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C) 1.51 ±0.06 V (TA = -40 to +105°C) Power-down-reset: 1.50 ±0.04 V (TA = -40 to +85°C) 1.50 ±0.06 V (TA = -40 to +105°C) 				
Voltage detector		1.63 V to 4.06 V (14 stages)				
On-chip debug fu	nction	Provided				
Power supply volt	age	V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C) V _{DD} = 2.4 to 5.5 V (T _A = -40 to +105°C)				
Operating ambier	nt temperature	T _A = -40 to +85°C (A: Consumer applications, D: Industrial applications), T _A = -40 to +105°C (G: Industrial applications)				

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Items	Items Symbol Conditions				TYP.	MAX.	Unit
Output voltage, high	Vон1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -10.0 mA	EVDD0 - 1.5			٧
		P80 to P87, P100 to P102, P110,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA	EVDD0 - 0.7			V
		P111, P120, P130, P140 to P147	1.8 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -1.5 mA	EVDD0 - 0.5			V
			1.6 V ≤ EV _{DD0} < 1.8 V, IOH1 = -1.0 mA	EVDD0 - 0.5			٧
	VOH2	P20 to P27, P150 to P156	1.6 V \leq VDD \leq 5.5 V, IOH2 = -100 μA	VDD - 0.5			V
Output voltage, low	Vol1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 20.0 mA			1.3	٧
	· · · · · · · · · · · · · · · · · · ·	P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 8.5 mA			0.7	٧
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 3.0 mA			0.6	V
		L2 P20 to P27, P150 to P156	2.7 V ≤ EVDD0 ≤ 5.5 V, loL1 = 1.5 mA			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IOL1} = 0.6 \text{ mA}$			0.4	٧
			1.6 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 0.3 mA			0.4	V
	VOL2		$1.6 \text{ V} \le \text{Vdd} \le 5.5 \text{ V},$ $\text{Iol2} = 400 \ \mu\text{A}$			0.4	٧
	Vol.3 P60 to P63	P60 to P63	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 15.0 mA			2.0	V
			4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 5.0 mA			0.4	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 3.0 mA			0.4	V
			1.8 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 2.0 mA			0.4	V
			1.6 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 1.0 mA			0.4	V

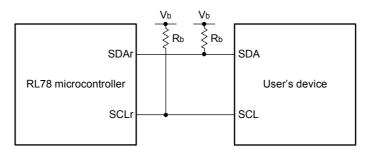
Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

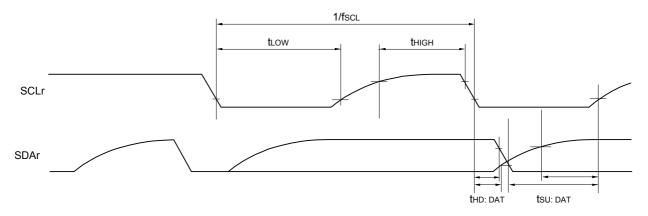
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- Note 8. Current flowing during programming of the data flash.
- Note 9. Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 23.3.3 SNOOZE mode in the RL78/G14 User's Manual.
- **Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- Note 12. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Note 13. A comparator and D/A converter are provided in products with 96 KB or more code flash memory.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. $Rb[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01, 10, 11, 20, 30, 31), g: PIM, POM number (g = 0, 1, 3 to 5, 14)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0, 2), mn = 00, 01, 02, 10, 12, 13)

2.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

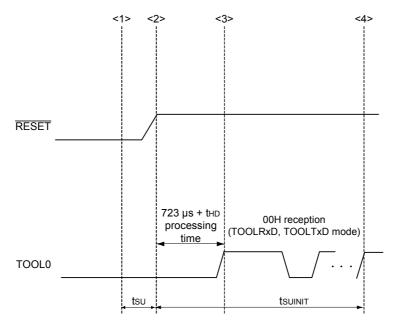
Parameter	Symbol	Conditions		HS (high-sp mo	,	LS (low-sp mo	eed main) ode	,	ltage main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fscL	Standard mode:	2.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
frequency		fc∟k ≥ 1 MHz	1.8 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EVDD0 ≤ 5.5 V	_	_	0	100	0	100	kHz
Setup time of	tsu: sta	2.7 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
restart condition		1.8 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		_	_	4.7		4.7		μs
Hold time Note 1	thd: STA	2.7 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ \$	5.5 V	_	_	4.0		4.0		μs
Hold time when	tLOW	2.7 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
SCLA0 = "L"		1.8 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ \$	5.5 V	_	_	4.7		4.7		μs
Hold time when	thigh	2.7 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
SCLA0 = "H"		1.8 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ \$	5.5 V	_	_	4.0		4.0		μs

(Notes, Caution, and Remark are listed on the next page.)

2.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
thd: How long to keep the TOOL0 pin at the low level from when the external resets end
(excluding the processing time of the firmware to control the flash memory)

3.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operat-	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V _{DD} = 5.0 V		2.4		mA
current		ing mode	mode Note 5	fiH = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.4		
Note 1	Note 1		fHOCO = 32 MHz,	Basic	V _{DD} = 5.0 V		2.1			
			fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.1			
			HS (high-speed main)	fHOCO = 64 MHz,	Normal	V _{DD} = 5.0 V		5.1	9.3	mA
			mode Note 5	fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		5.1	9.3	
				fHOCO = 32 MHz,	Normal	V _{DD} = 5.0 V		4.8	8.7	
				fiH = 32 MHz Note 3	operation	V _{DD} = 3.0 V		4.8	8.7	
				fносо = 48 MHz,	Normal	V _{DD} = 5.0 V		4.0	7.3	
				fiH = 24 MHz Note 3	operation	V _{DD} = 3.0 V		4.0	7.3	
				fHOCO = 24 MHz,	Normal	V _{DD} = 5.0 V		3.8	6.7	
				fiH = 24 MHz Note 3	operation	V _{DD} = 3.0 V		3.8	6.7	
				fHOCO = 16 MHz,	Normal	V _{DD} = 5.0 V		2.8	4.9	
				fih = 16 MHz Note 3 ope	operation	V _{DD} = 3.0 V		2.8	4.9	
		,	f _{MX} = 20 MHz Note 2,	Normal	Square wave input		3.3	5.7	mA	
				V _{DD} = 5.0 V	operation	Resonator connection		3.4	5.8	
				V _{DD} = 3.0 V f _{MX} = 10 MHz Note 2,	Normal operation	Square wave input		3.3	5.7	
						Resonator connection		3.4	5.8	
					Normal	Square wave input		2.0	3.4	
					operation	Resonator connection		2.1	3.5	
				fmx = 10 MHz Note 2,	Normal	Square wave input		2.0	3.4	
				V _{DD} = 3.0 V	operation	Resonator connection		2.1	3.5	
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μΑ
			operation	TA = -40°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	
				T _A = +25°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4		Square wave input		4.8	6.7	
			T _A = +50°C	operation	Resonator connection		4.8	6.7		
			fsuB = 32.768 kHz Note 4		Square wave input		4.8	7.5		
			T _A = +70°C	operation	Resonator connection		4.8	7.5		
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9		
				T _A = +85°C	operation	Resonator connection		5.4	8.9]]
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		7.2	21.0	
				T _A = +105°C	operation	Resonator connection		7.3	21.1	

(Notes and Remarks are listed on the next page.)

3.4 AC Characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

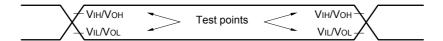
Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min-	Tcy	Main system	HS (high-speed main)	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	0.03125		1	μs
imum instruction exe- cution time)		clock (fmain) operation	mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		Subsystem clo	ock (fsub) operation	$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	0.03125		1	μs
		program- ming mode	mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock	fex	2.7 V ≤ V _{DD} ≤	5.5 V		1.0		20.0	MHz
frequency		2.4 V ≤ V _{DD} ≤	2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock	texH,	2.7 V ≤ V _{DD} ≤	5.5 V		24			ns
input high-level width,	texL	2.4 V ≤ V _{DD} ≤	2.7 V		30			ns
low-level width	texhs, texhs				13.7			μs
TI00 to TI03, TI10 to TI13 input high-level width, low-level width	ttih, ttil				1/fMCK + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	100			ns
				2.4 V ≤ EVDD0 < 2.7 V	300			ns
Timer RJ input high-	tтлін,	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	40			ns
level width, low-level width	t⊤JIL			2.4 V ≤ EVDD0 < 2.7 V	120			ns

Note The following conditions are required for low voltage interface when EVDD0 < VDD $2.4 \text{ V} \le \text{EVDD0} < 2.7 \text{ V}$: MIN. 125 ns

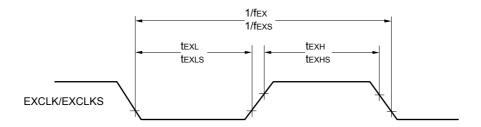
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))

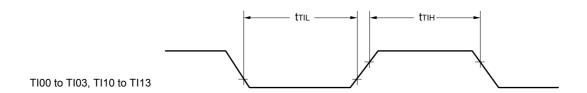
AC Timing Test Points

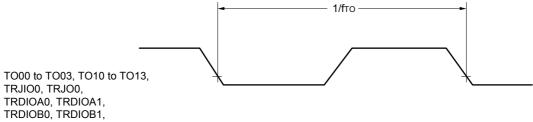


External System Clock Timing



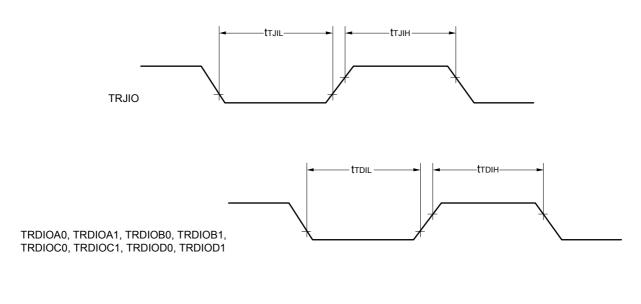
TI/TO Timing

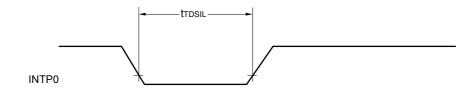


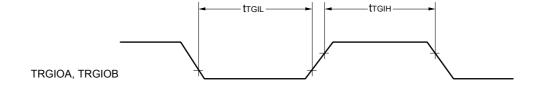


TRDIOCO, TRDIOC1, TRDIODO, TRDIOD1,

TRGIOA, TRGIOB







(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) Note	tsıĸ1	$ 4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 1.4 \text{ k}\Omega $	88		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	88		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$	220		ns
SIp hold time (from SCKp↓) Note	tksi1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega$	38		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	38		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	38		ns
Delay time from SCKp↑ to SOp output Note	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega$		50	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		50	ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega$		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

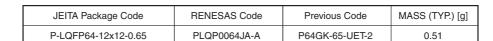
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

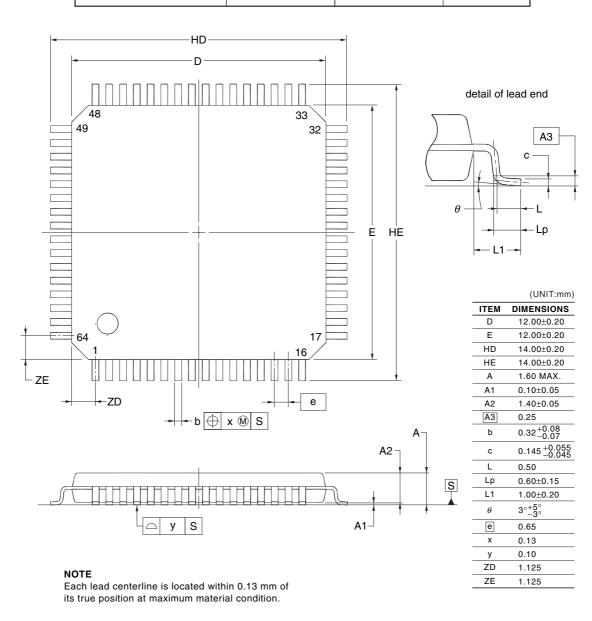
(Remarks are listed on the next page.)

(3/3)

4.8 64-pin products

R5F104LCAFA, R5F104LDAFA, R5F104LEAFA, R5F104LFAFA, R5F104LGAFA, R5F104LHAFA, R5F104LJAFA R5F104LCDFA, R5F104LDDFA, R5F104LEDFA, R5F104LFDFA, R5F104LGGFA, R5F104LHDFA, R5F104LJDFA R5F104LCGFA, R5F104LDGFA, R5F104LEGFA, R5F104LFGFA, R5F104LGGFA, R5F104LHGFA, R5F104LJGFA R5F104LKAFA, R5F104LLAFA R5F104LKGFA, R5F104LLGFA



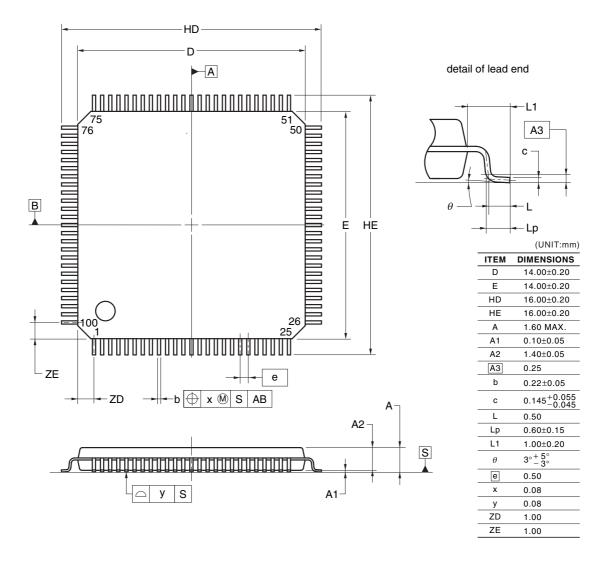


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4.10 100-pin products

R5F104PFAFB, R5F104PGAFB, R5F104PHAFB, R5F104PJAFB R5F104PFDFB, R5F104PGDFB, R5F104PHDFB, R5F104PJDFB R5F104PFGFB, R5F104PGGFB, R5F104PHGFB, R5F104PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]	
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69	



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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.